



Bipolar NPN Bare Die – BTN6085

Part Description

The BTN6085 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. PNP Complement is BTP6085.

Key Parameters:

- VCBO = 40V
- VCEO = 25V
- VEBO = 6V
- hFE = 85-300 @ VCE = 1V, IC = 0.1A
- VCE(Sat) = 0.5V @ IC = 0.8A, IB = 80mA
- fT = 100 MHz @ VCE = 10V, IE = 0A
- COBO = 6pF @ VCB = 10V

Features

Low VCE(sat). Designed to provide performance equivalent to ON Semi SS8050

Die Size (Unseen)

450µm X 450µm, 18 Mils X 18 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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